

AMENDMENTS TO THE CLAIMS

1. (Currently amended) A semiconductor apparatus, comprising:
 - a semiconductor substrate;
 - an electrode pad including a metal layer and formed ~~on~~ over the semiconductor substrate;
 - a MOS transistor formed ~~on~~ over the semiconductor substrate; and
 - an analog circuit formed in a region under the electrode pad, said analog circuit formed over ~~on~~ the semiconductor substrate and comprising a resistive element including a semiconductor material.
2. (Currently amended) [[A]] The semiconductor apparatus according to Claim 1, wherein the resistive element includes a specific material made of one of polysilicon, silicon germanium, and silicon chrome.
3. (Currently amended) [[A]] The semiconductor apparatus according to Claim 1, wherein the resistive element includes a plurality of resistors.
4. (Currently amended) [[A]] The semiconductor apparatus according to Claim 1, wherein the MOS transistor comprises a gate electrode including a specific material of the resistive element.
5. (Currently amended) [[A]] The semiconductor apparatus according to Claim 1, further comprising:
 - an insulating film formed on the semiconductor substrate in a region in a vicinity of the electrode pad; and
 - a fuse element formed on the insulating film.

6. (Currently amended) [[A]] The semiconductor apparatus according to Claim 5, wherein the ~~insulating film~~ fuse element includes a specific material of the resistive element.

7. (Currently amended) [[A]] The semiconductor apparatus according to Claim 5, further comprising:

a rerouting layer formed in a region above the fuse element; and

an external connection terminal formed on the rerouting layer in a region different from a formation region of the electrode pad.

8. (Currently amended) [[A]] The semiconductor apparatus according to Claim 5, wherein the analog circuit comprises a voltage setting circuit, the resistive element comprises at least two resistors for producing a split voltage based on an input source power voltage, and the voltage setting circuit changes the split voltage according to a condition of the fuse element.

9. (Currently amended) [[A]] The semiconductor apparatus according to Claim 1, wherein the resistive element comprises at least two resistors for producing a split voltage based on an input source power voltage, the analog circuit comprises a reference voltage generator for generating a reference voltage and a voltage detector including a comparator for performing a comparison of the split voltage with the reference voltage.

10. (Currently amended) [[A]] The semiconductor apparatus according to Claim 9, wherein the analog circuit further comprises an output driver for controlling an output voltage based on an input voltage, and the comparator of the voltage detector outputs a gate control voltage as a result of the comparison for controlling the output driver to control the output voltage.

Claims 11 – 16 (Canceled).

17. (Currently amended) [[A]] The semiconductor apparatus according to Claim 1, wherein the resistive element includes a plurality of doped semiconductor material resistors.

18. (Currently amended) [[A]] The semiconductor apparatus according to Claim 4, wherein said gate electrode has lengthwise ends which are bent in an upward direction ~~towards said electrode pad~~ over an insulating film.